

EAST - [09829969.wsp.1]

File View Edit Tools Window Help

Drafts  
Pending  
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L1: (1171) MOS and (metal with silicide an  
L2: (150) 1 and (silicide with nm)  
L3: (15) 1 and (silicide with "5" adj nm)  
L4: (19) 1 and (silicide with "20" adj nm)  
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DBs: USPAT, EPO, JPO, DERWENT, IBM, TDB

Plurals

Default operator: OR

Highlight all hit terms initially

1 and (silicide with "20" adj nm)

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6657265 B2	20031202	25	Semiconductor device and its manufacturing method	257/380	257/381; 257/384;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6642087 B2	20031104	23	Solid state imaging device having a photodiode and a MOSFET and method of	438/149	257/231; 257/232;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6570222 B2	20030527	25	Solid state imaging device having a photodiode and a MOSFET	257/347	257/223; 257/233;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6566254 B1	20030520	12	Method for forming a silicide film on gate electrodes and diffusion layers of MOS	438/660	438/664
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6562724 B1	20030513	6	Self-aligned stack formation	438/735	438/736; 438/745;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6503803 B2	20030107	56	Method of fabricating a semiconductor integrated circuit device for connecting	438/296	257/E23.019; 257/E23.145;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6268658 B1	20010731	54	Semiconductor integrated circuit device for connecting semiconductor region and	257/763	257/764; 257/767;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6248638 B1	20010619	7	Enhancements to polysilicon gate	438/305	257/E21.196; 257/E21.199;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6114736 A	20000905	24	Controlled dopant diffusion and metal contamination in thin polycide gate	257/412	257/384; 257/751;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6031288 A	20000229	55	Semiconductor integrated circuit device for connecting semiconductor region and	257/754	257/755; 257/763;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6008124 A	19991228	26	Semiconductor device having improved lamination-structure reliability for buried	438/653	257/E21.199; 257/E21.433;